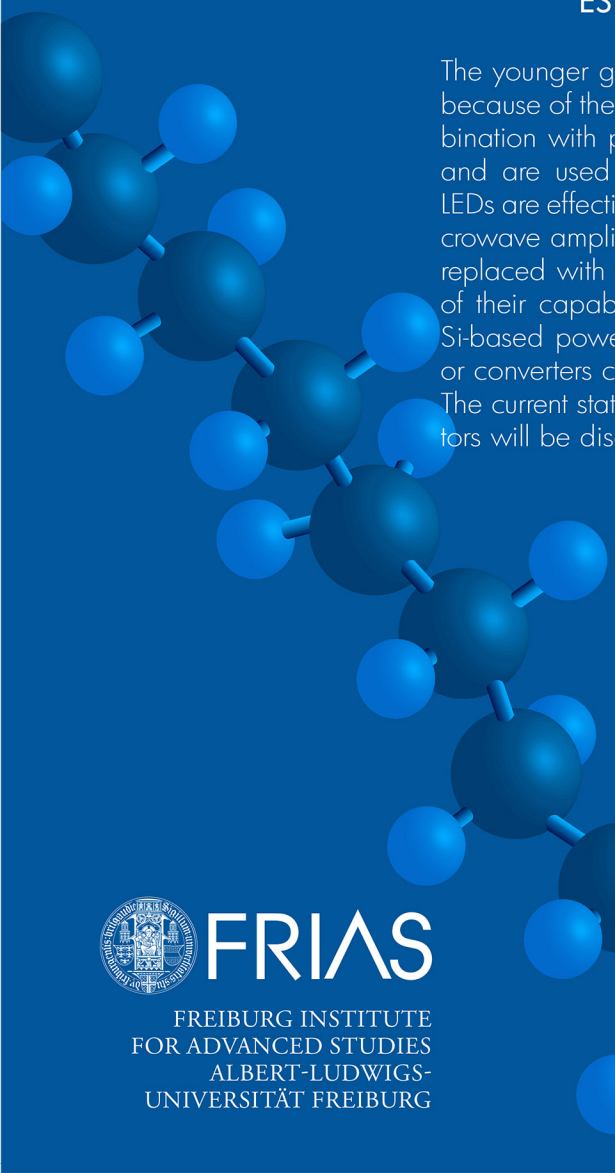
23RD HERMANN STAUDINGER LECTURE

NOBEL PRIZE LAUREATES AT FRIAS

HIROSHI AMANO

CENTER FOR INTEGRATED RESEARCH OF FUTURE ELECTRONICS (CIRFE) NAGOYA UNIVERSITY, JAPAN

NITRIDE-BASED FUTURE ELECTRONICS FOR ESTABLISHING A SUSTAINABLE SOCIETY



The younger generation can enjoy full-color portable games because of the emergence of GaN-based blue LEDs. In combination with phosphors, they can act as white light source and are used in general lighting. AlGaN-based deep-UV LEDs are effective for sterilization and purification of water. Microwave amplifiers employing GaAs-based HFETs are being replaced with those employing GaN-based HFETs because of their capability of higher-power operation. By replacing Si-based power devices, the average efficiency of inverters or converters can be improved from 95% to more than 99%. The current status of our understanding of nitride semiconductors will be discussed.

Thursday, March 16, 2017
4:15 p.m.
Anatomy Lecture Hall
Albertstraße 19, Freiburg

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